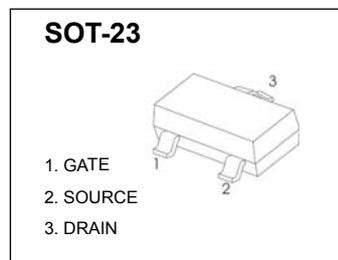


UMW SI2300A N-Channel 20-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
20V	25mΩ@4.5V	6A
	34.5mΩ@2.5V	



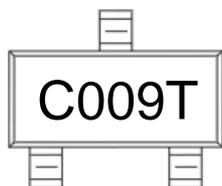
**FEATURE**

- TrenchFET Power MOSFET

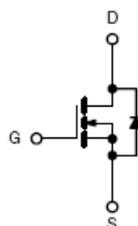
**APPLICATION**

- Load Switch for Portable Devices
- DC/DC Converter

**MARKING**



**Equivalent Circuit**



**Maximum ratings ( $T_a=25^{\circ}C$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	±12	
Continuous Drain Current	$I_D$	6	A
Continuous Source-Drain Current(Diode Conduction)	$I_S$	0.6	
Power Dissipation	$P_D$		W
Thermal Resistance from Junction to Ambient ( $t \leq 5s$ )	$R_{\theta JA}$	312.5	$^{\circ}C/W$
Operating Junction	$T_J$	150	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55 ~ +150	

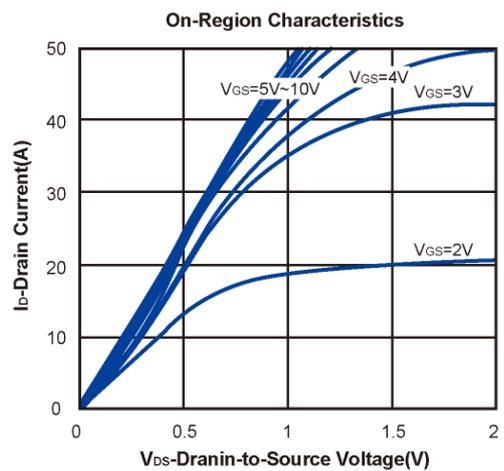
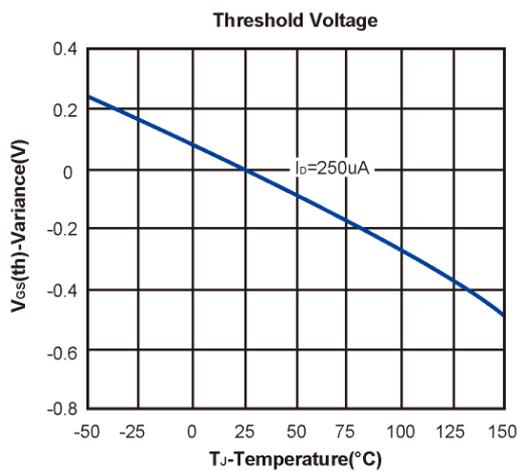
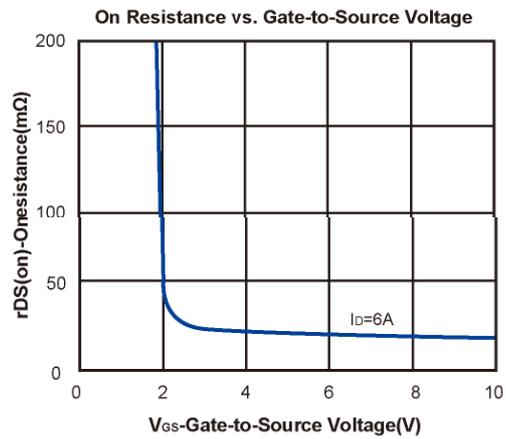
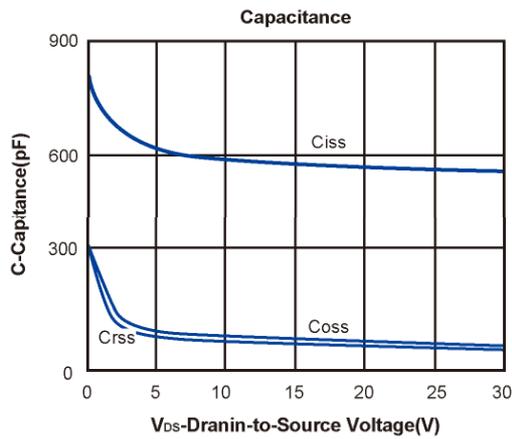
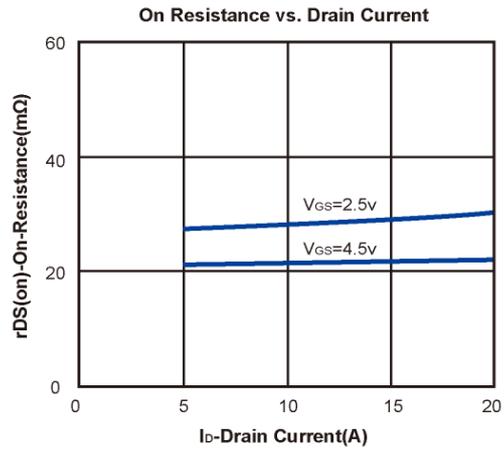
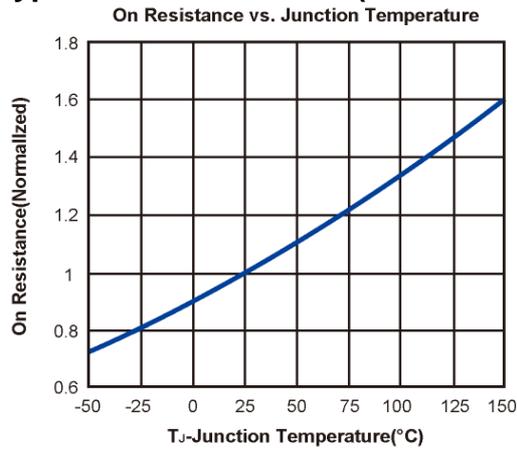
$T_a=25\text{ }^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 10\mu A$	20			V
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 50\mu A$	0.40		1	
Gate-body leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 8V$			$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 20V, V_{GS} = 0V$			1	$\mu A$
Drain-source on-resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 4.5V, I_D = 6A$		0.021	0.025	$\Omega$
		$V_{GS} = 2.5V, I_D = 5.2A$		0.028	0.034	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 5V, I_D = 3.6A$		8		S
Diode forward voltage	$V_{SD}$	$I_S = 0.94A, V_{GS} = 0V$		0.74	1.2	V
<b>Dynamic</b>						
Total gate charge	$Q_g$	$V_{DS} = 10V, V_{GS} = 4.5V, I_D = 3.6A$		7.7	10	nC
Gate-source charge	$Q_{gs}$			0.32		
Gate-drain charge	$Q_{gd}$			2.1		
Input capacitance <sup>b</sup>	$C_{iss}$	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		574		pF
Output capacitance <sup>b</sup>	$C_{oss}$			70		
Reverse transfer capacitance <sup>b</sup>	$C_{rss}$			60		
<b>Switching<sup>b</sup></b>						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 10V,$ $R_L = 5.5\Omega, I_D \approx 3.6A,$ $V_{GEN} = 4.5V, R_g = 6\Omega$		78.7		ns
Rise time	$t_r$			128		
Turn-off delay time	$t_{d(off)}$			453		
Fall time	$t_f$			80.9		

**Notes :**

- a. Pulse Test : Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- b. These parameters have no way to verify.

### Typical Characteristics (T<sub>J</sub> =25°C Noted)



Typical Characteristics (T<sub>J</sub> =25°C Noted)

